

## CSM1020N4S223

### 100V N-Channel Enhancement Mode MOSFET

**Voltage**

**100 V**

**Current**

**4A**

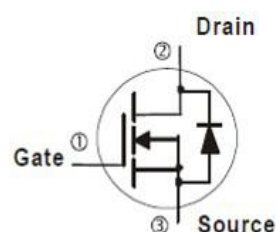
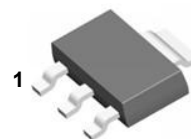
#### Features

- $R_{DS(ON)}$ ,  $V_{GS}@10V$ ,  $I_D@2.5A < 140m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}@6V$ ,  $I_D@1A < 180m\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance

#### Mechanical Data

- Case : SOT-223 Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.043 ounces, 0.123 grams

SOT-223



### Maximum Ratings and Thermal Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		$V_{DS}$	100	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	
Continuous Drain Current (Note 4)	$T_C=25^\circ\text{C}$	$I_D$	4	A
Pulsed Drain Current (Note 1)	$T_C=25^\circ\text{C}$	$I_{DM}$	16	
Power Dissipation	$T_C=25^\circ\text{C}$	$P_D$	8	W
Continuous Drain Current (Note 4)	$T_A=25^\circ\text{C}$	$I_D$	3.1	A
Power Dissipation	$T_A=25^\circ\text{C}$	$P_D$	3.1	W
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~150	$^\circ\text{C}$
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{\theta JC}$	15.6	$^\circ\text{C/W}$
	Junction to Ambient	$R_{\theta JA}$	40.3	

- Limited only By Maximum Junction Temperature

# CSM1020N4S223

## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	100	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	2	2.76	3.5	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =2.5A	-	110	140	mΩ
		V <sub>GS</sub> =6V, I <sub>D</sub> =1A	-	120	180	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V	-	-	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =+20V, V <sub>DS</sub> =0V	-	-	+100	nA
Dynamic (Note 6)						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =37.5V, I <sub>D</sub> =5A, V <sub>GS</sub> =10V (Note 2,3)	-	12	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	3.1	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	2.2	-	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, f=1MHZ	-	707	-	pF
Output Capacitance	C <sub>oss</sub>		-	40	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	16	-	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DS</sub> =37.5V, R <sub>L</sub> =7.5Ω, V <sub>GS</sub> =10V, R <sub>G</sub> =3Ω (Note 2,3)	-	6	-	ns
Turn-On Rise Time	t <sub>r</sub>		-	27	-	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	15	-	
Turn-Off Fall Time	t <sub>f</sub>		-	7	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I <sub>s</sub>	---	-	-	5	A
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1A, V <sub>GS</sub> =0V	-	0.78	1	V

### NOTES :

1. Pulse width≤300us, Duty cycle≤2%.
2. Essentially independent of operating temperature typical characteristics.
3. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub>=25°C.
4. The maximum current rating is package limited.
5. R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
6. Guaranteed by design, not subject to production testing.

## CSM1020N4S223

### TYPICAL CHARACTERISTIC CURVES

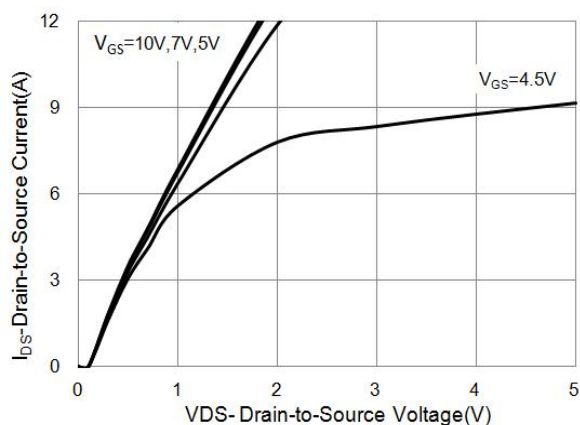


Fig.1 Output Characteristics

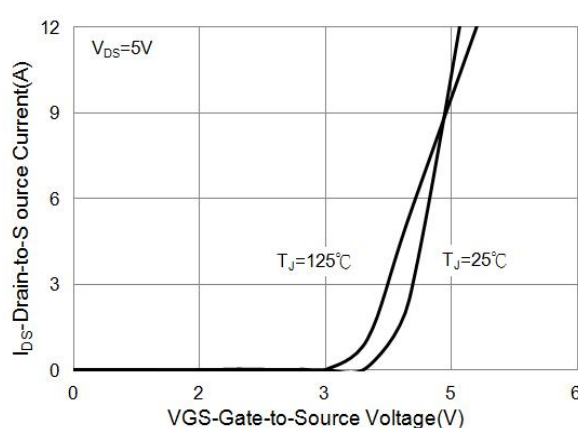


Fig.2 Transfer Characteristics

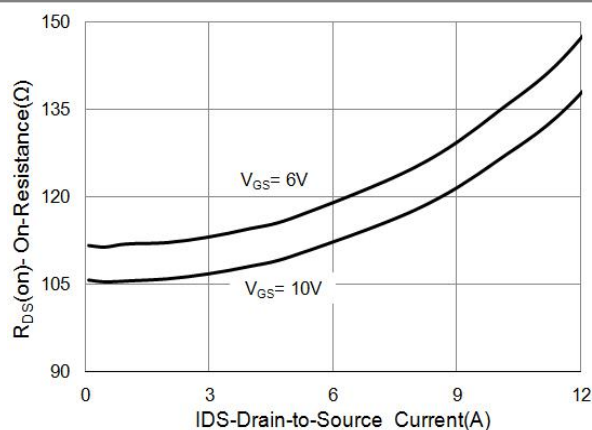


Fig.3 On-Resistance vs. Drain Current

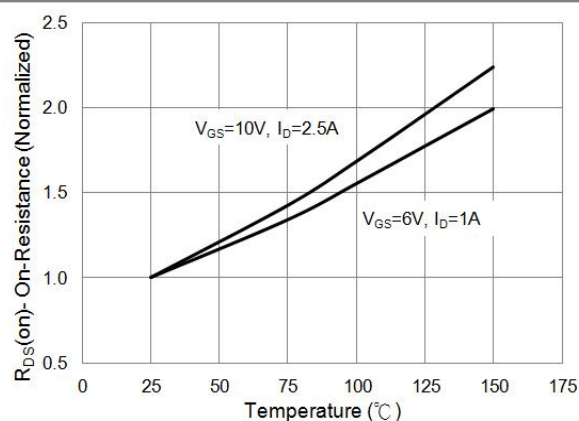


Fig.4 On-Resistance vs. Junction temperature

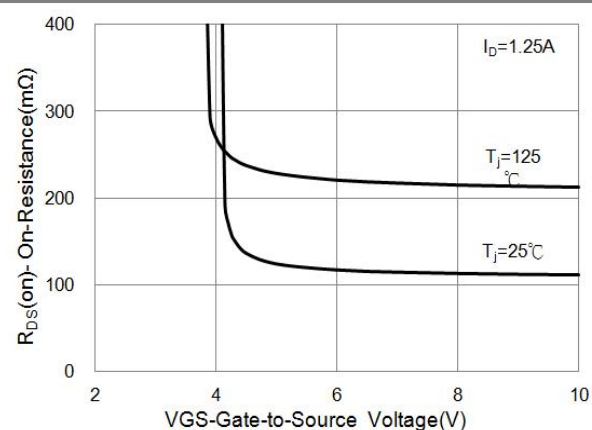


Fig.5 On-Resistance Variation with  $V_{GS}$

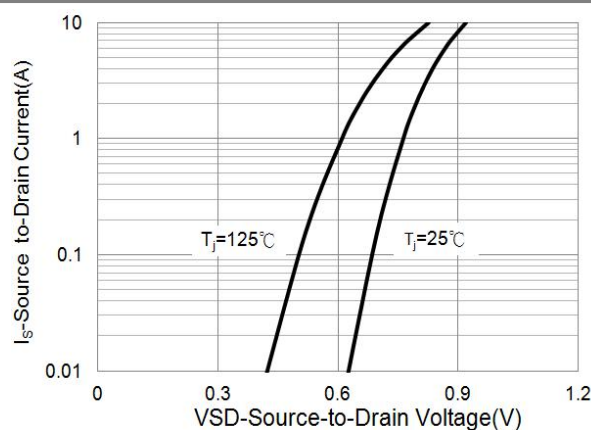


Fig.6 Source-Drain Diode Forward Voltage

## CSM1020N4S223

### TYPICAL CHARACTERISTIC CURVES

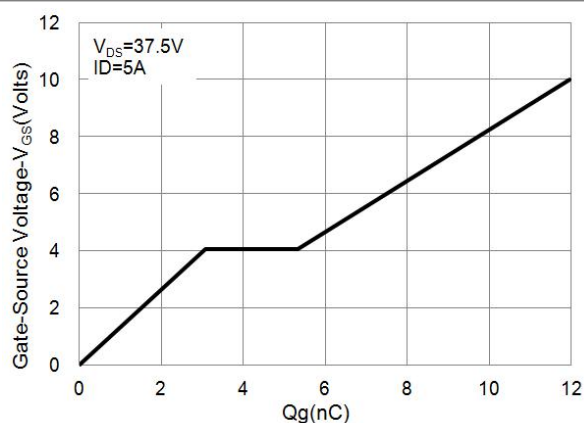


Fig.7 Gate-Charge Characteristics

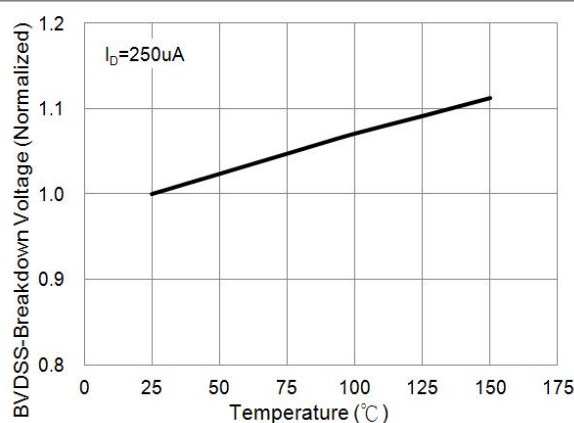


Fig.8 Breakdown Voltage Variation vs. Temperature

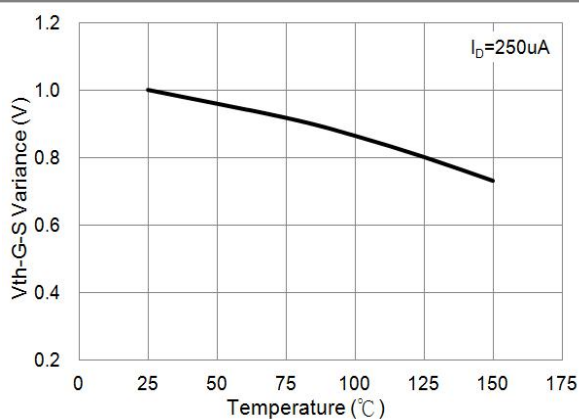


Fig.9 Threshold Voltage Variation with Temperature

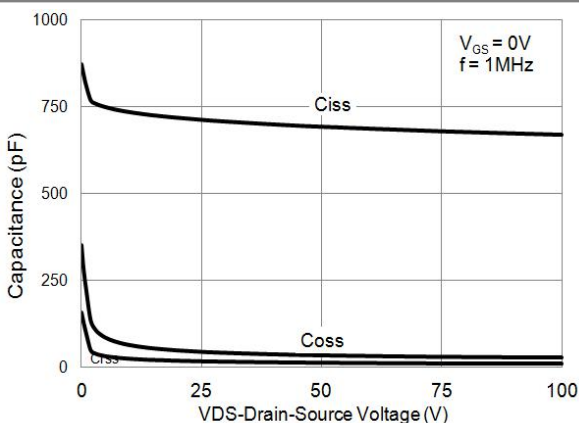


Fig.10 Capacitance vs. Drain-Source Voltage

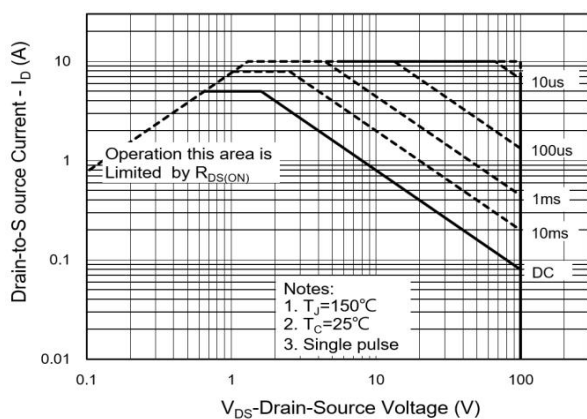


Fig.11 Maximum Safe Operating Area

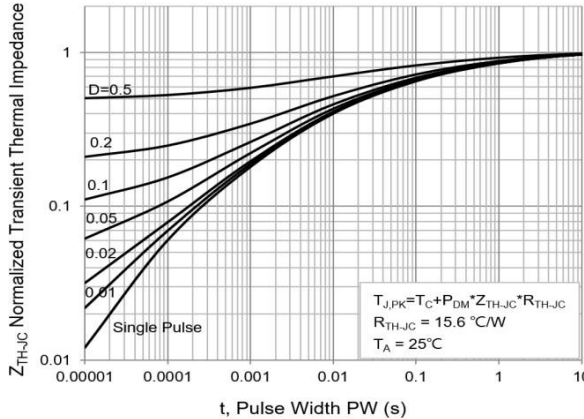
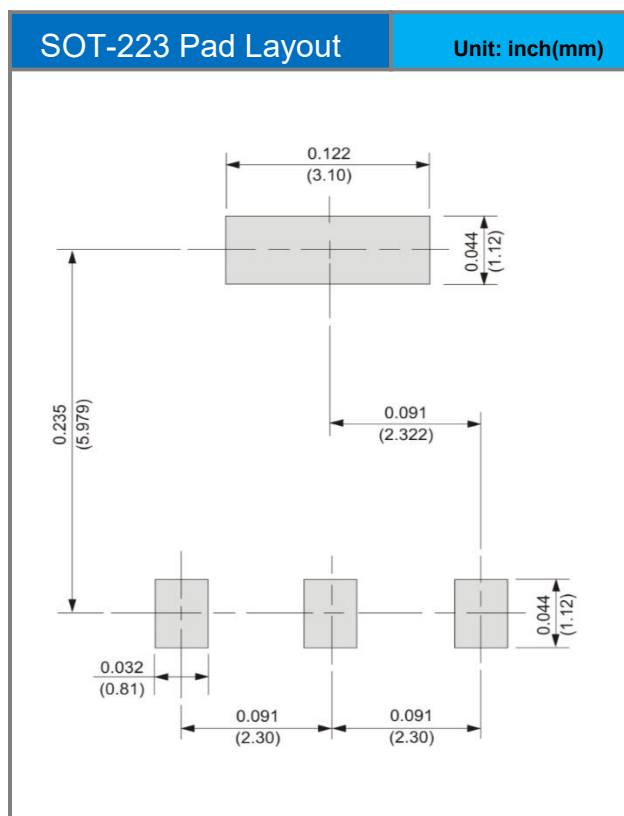
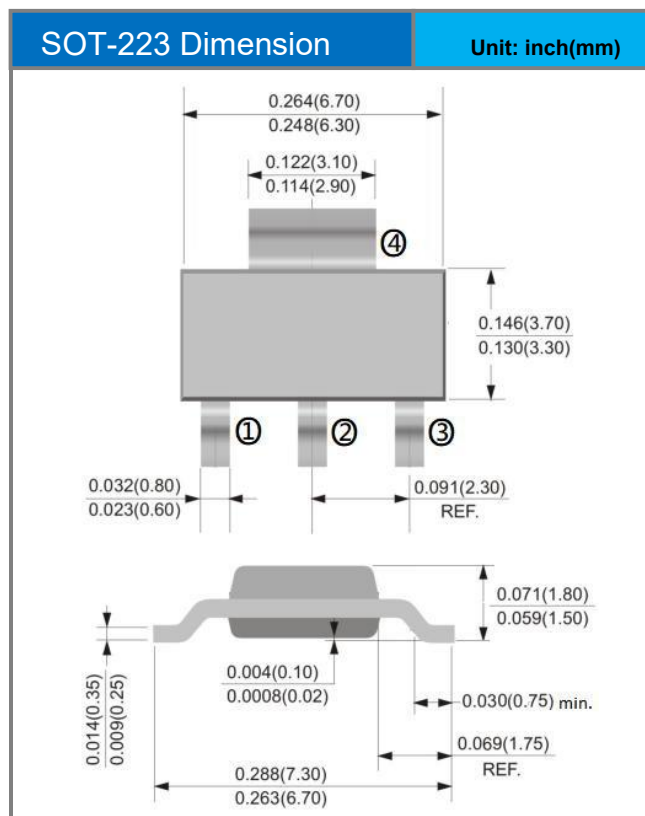


Fig.12 Normalized Transient Thermal Impedance

## CSM1020N4S223

### Packaging Information & Mounting Pad Layout



### Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type
CSM1020N4S223	SOT-223	1,000pcs / 13" reel

## **CSM1020N4S223**

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